



BC808

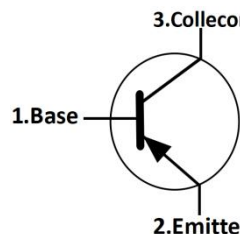
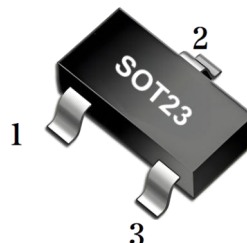
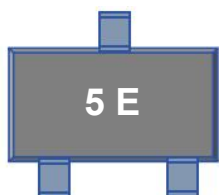
PNP SILICON TRANSISTOR

FEATURES

- * Suitable for AF-Driver stages and low power output stages
- * Complement to BC818

MARKING

Type Code: Marking: 5E/5F/5G



ABSOLUTE MAXIMUM RATINGS (Tc=25°C, unless otherwise specified)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CB0}	Collector-base voltage	-30	V
V _{CE0}	Collector-emitter voltage	-25	V
V _{EB0}	Emitter-base voltage	-5	V
I _C	Collector Current - Continuous	-0.8	A
P _C	Collector Power Dissipation	0.3	W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

ELECTRICAL CHARACTERISTICS (Tc=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	BV _{CB0}	I _C = -100μA, I _B =0	-30			V
Collector-emitter breakdown voltage	BV _{CE0}	I _C =-10mA, I _E =0	-25			V
Emitter-base breakdown voltage	BV _{EB0}	I _E =-100μA, I _C =0	-5			V
Collector cut-off current	I _{CB0}	V _{CB} =-25V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EB0}	V _{EB} =-4V, I _C =0			-0.1	μA
DC Current Gain (CLASSIFICATION OF h _{FE1})	h _{FE1}	V _{CE} =-1V, I _C =-100 mA	100		250	
			160		400	
			250		630	
	h _{FE2}	V _{CE} =-1V, I _C =-300mA	60			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-500mA, I _B =-50mA			-0.7	V
Base-emitter voltage	V _{BE(sat)}	V _{CE} =-1V, I _C =-300mA			-1.2	V
Transition frequency	f _T	V _{CE} =-5V, I _C =-10mA, f=50MHz		100		MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz		12		pF



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■ TYPICAL CHARACTERISTICS

Fig. 1 Output Characteristics Curve

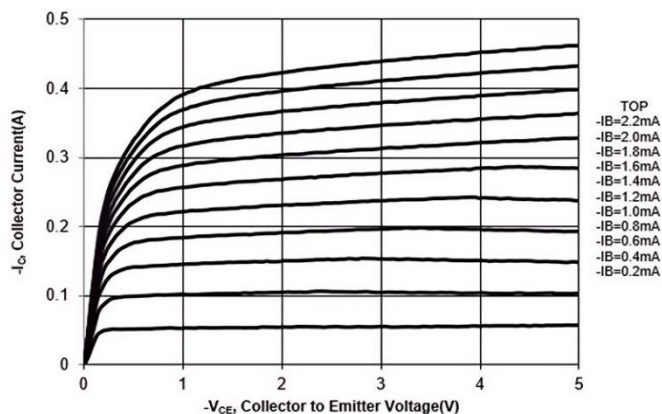


Fig. 2 Collector Current vs. Base to Emitter

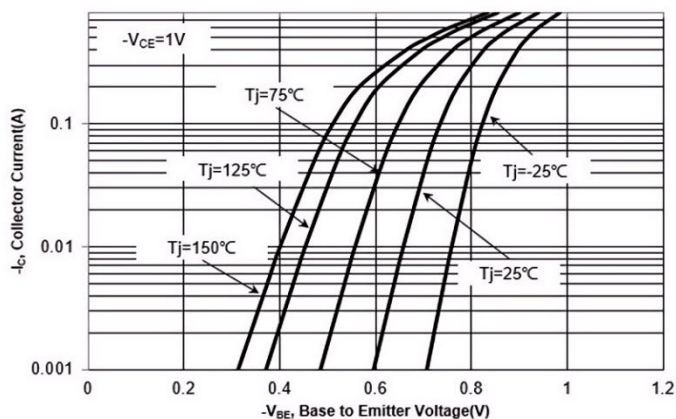


Fig. 3 DC Current Gain vs. Collector Current

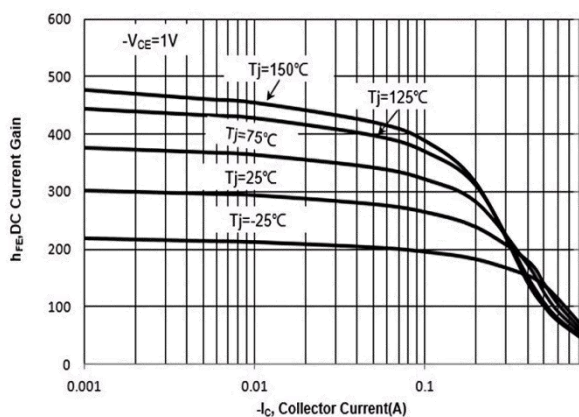


Fig. 4 V_{BESAT} vs. Collector Current

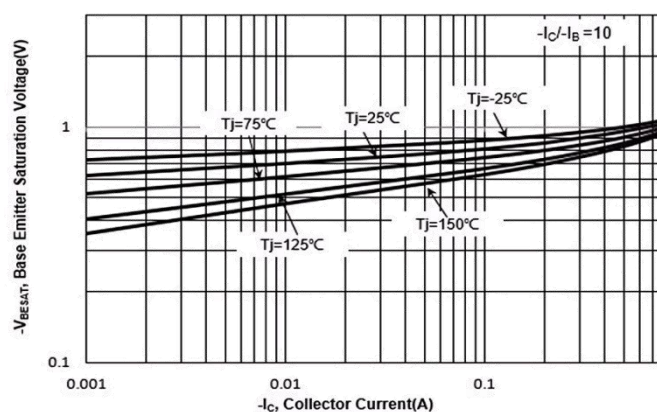


Fig. 5 V_{CESAT} vs. Collector Current

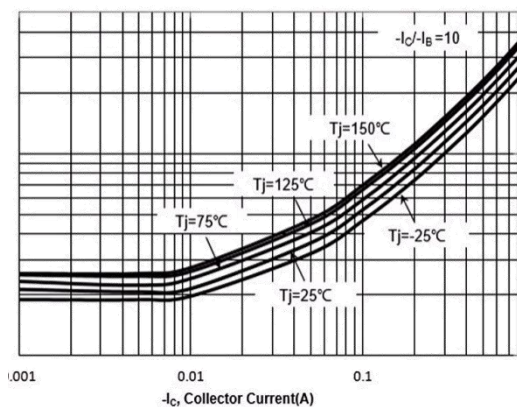
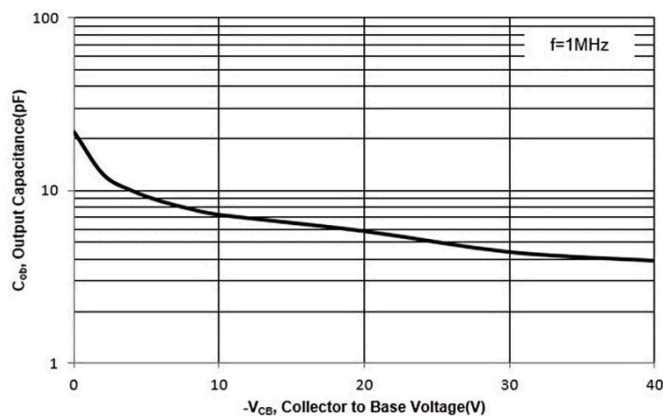


Fig. 6 Output Capacitance



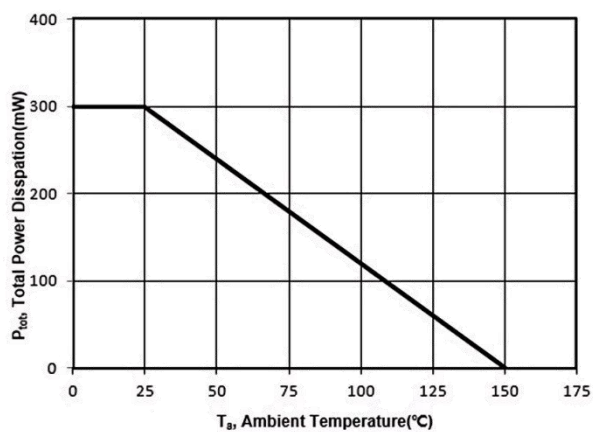


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■ TYPICAL CHARACTERISTICS

Fig 7. Power Derating Curve

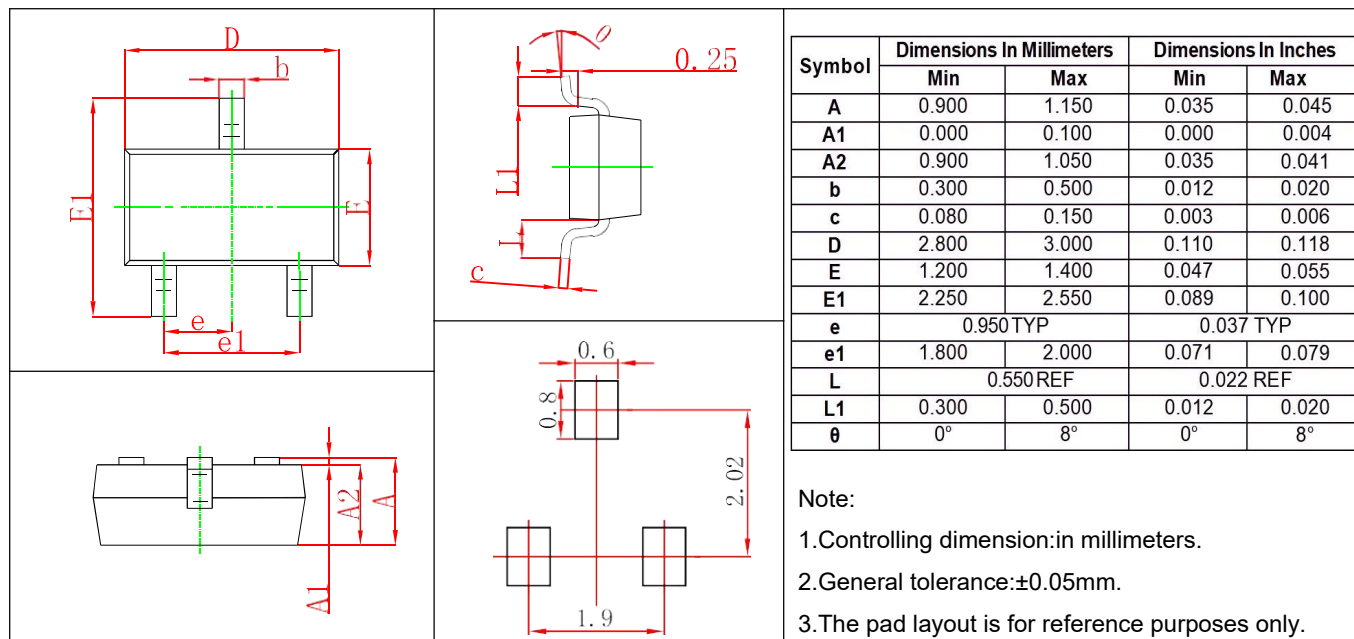




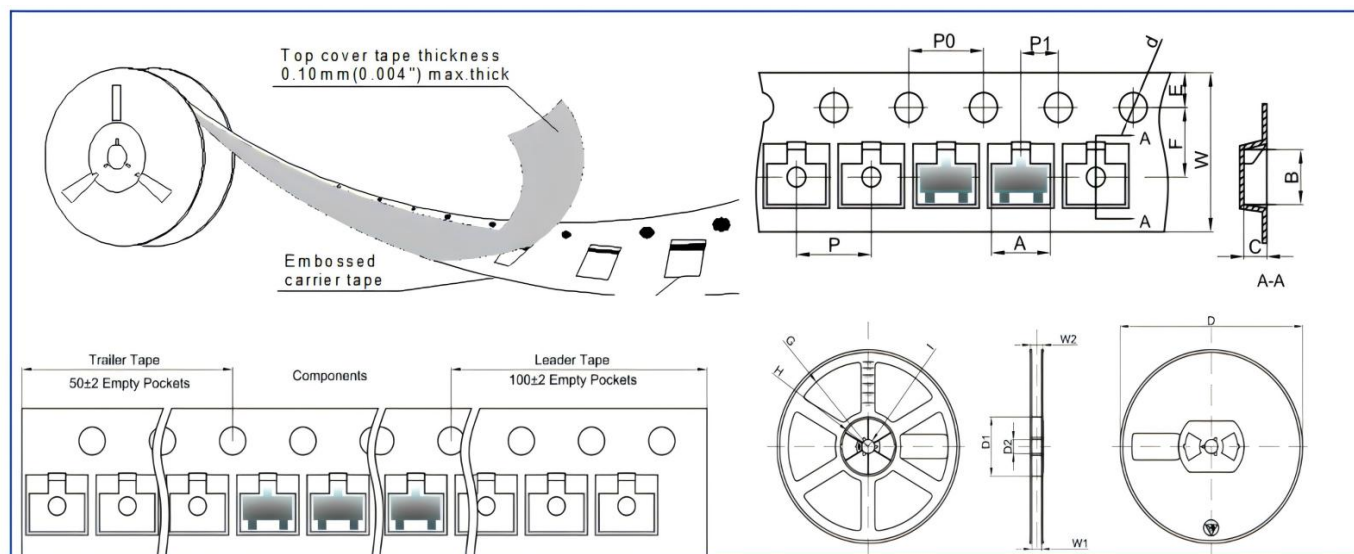
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PNP SILICON TRANSISTOR

SOT23 PACKAGE OUTLINE DIMENSIONS



REEL PACKING



Dimensions are in millimeter

PKG TYPE	A	B	C	d	E	F	Po	P	P1	W
SOT-23	3.15	2.77	1.22	Φ1.50	1.75	3.50	4.00	4.00	2.00	8.00
Reel Option	D	D1	D2	G	H	I	W1	W2	Q.TY PER REEL	
7" Dia	Φ178.0	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30	3000PCS	
13"Dia	φ330.0	/	13.00	/	/	R6.50	9.50	12.30	10000PCS	